

*REMARKS/ARGUMENTS*

In further supplementation of the Amendment filed August 24, 2006, and the Supplemental Amendment filed October 23, 2006 Applicants further clarify claim 14, place a corrected former limitation of that claim in newly added claim 23, and correct an error in the specification. Applicants' representative apologizes for this piecemeal response to the Office Action of May 2, 2006.

An error in the specification at page 28 is corrected. In the process illustrated in parts (a) – (i) of Figure 20, the steps from part (d) – (i) are repeated in a cycle after the steps of parts (a) – (i) are initially completed. To conform claim 14 to this correction, the final limitation of that claim is removed, corrected, and placed in new claim 23.

The remarks previously presented are maintained, except as to claim 14. To explain claim 14 as now presented, the following remarks are supplied and replace the former remarks concerning the former claim 14.

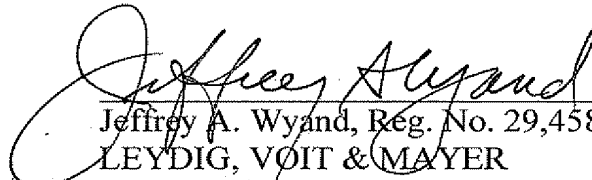
Independent method claim 14 is further amended to ensure that the claim conforms to the disclosure of the patent application with respect to Figure 20 and the description that appears in the patent application from page 27, line 9 through page 28, line 10. What is schematically illustrated in Figure 20 is a series of steps that are described in the claim 14. In the first step, parts (a) – (c) of Figure 20, the visible light pulse 24 irradiates a first part of the silicon film 203. Melting and recrystallization begins in response to that irradiation. In a second step, parts (d) and (f) of Figure 20, a second area, to the rear of the first area on the silicon film, is irradiated with the ultraviolet light pulse 25. In a s third step, although not illustrated, but described in the text of the patent application, the structure 9 in Figure 20 moves to the left in Figure 20, along the direction of the arrow 71. In a fourth step, parts (g) – (i) of Figure 20, the pulsed visible light 24n, where n indicates a sequential process, is applied to a rear part of the first irradiated area and to a front part of the second irradiated area. As described in the patent application at page 28, this process aids in

the continuing crystallization at the region 31, shown in part (h) of Figure 20. In other words, the molten region continues to shift toward the right in the figure as the structure 9 moves toward the left.

After this four step process, the last three steps of the process illustrated in Figure 20, without the first step, are continually repeated in a cycle, as explained in new claim 23. That added cycle results in the growth of a high quality crystalline silicon film. That cyclic process includes

Entry and consideration of these further supplemental amendments are earnestly solicited.

Respectfully submitted,

  
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